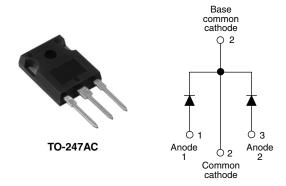


Vishay High Power Products

HEXFRED® Ultrafast Soft Recovery Diode, 2 x 16 A



PRODUCT SUMMARY					
V _R per leg	1200 V				
V _F at 16 A at 25 °C	3.0 V				
I _{F(AV)}	2 x 16 A				
t _{rr} (typical) per leg	5.8 A				
T _J (maximum)	150 °C				
Q _{rr} (typical) per leg	260 nC				
IppM (typical) per leg	5.8 A				

FEATURES

- Ultrafast recovery
- · Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- · Specified at operating conditions
- · Designed and qualified for industrial level

BENEFITS

- · Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- · Higher frequency operation
- · Reduced snubbing
- Reduced parts count

DESCRIPTION

HFA32PA120C is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 16 A per leg continuous current, the HFA32PA120C is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA32PA120C is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V_{R}		1200	V		
Maximum continuous forward current per leg	1-	T _C = 100 °C	16			
per device	- I _F		32	Α		
Single pulse forward current	I _{FSM}		190	A		
Maximum repetitive forward current	I _{FRM}		64			
Maximum nauga dissination	P_{D}	T _C = 25 °C	151	°C		
Maximum power dissipation		T _C = 100 °C	60	C		
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	W		

HFA32PA120C

Vishay High Power Products





ELECTRICAL SPECIFICATIONS PER LEG (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	Ι _R = 100 μΑ		1200	-	-	
	V _{FM}	I _F = 16 A	See fig. 1	-	2.5	3.0	V
Maximum forward voltage		I _F = 32 A		-	3.2	3.93	
		I _F = 16 A, T _J = 125 °C		-	2.3	2.7	
Maximum reverse	,	$V_R = V_R$ rated		-	0.75	20	
leakage current	I _{RM}	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated See fig. 2		-	375	2000	μΑ
Junction capacitance	C _T	V _R = 200 V See fig. 3		=	27	40	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8.0 -		nΗ			

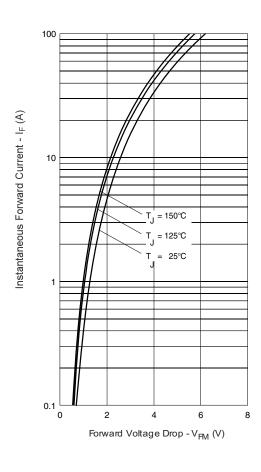
DYNAMIC RECOVERY CHARACTERISTICS PER LEG (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	30	-	ns
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C	25 °C		90	135	
occ lig. 5, 10	t _{rr2}	T _J = 125 °C		-	164	245	
Peak recovery current See fig. 6	I _{RRM1}	T _J = 25 °C	I _F = 16 A dI _F /dt = 200 A/μs V _R = 200 V	-	5.8	10	- A
	I _{RRM2}	T _J = 125 °C		-	8.3	15	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	260	675	
See fig. 7	Q _{rr2}	T _J = 125 °C		-	680	1838	IIC
Peak rate of fall of recovery	dI _{(rec)M} /dt1	T _J = 25 °C		_	120	-	- A/μs
current during t _b See fig. 8	dI _{(rec)M} /dt2	T _J = 125 °C		-	76	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R _{thJC}		-	-	0.83	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount		-	80	K/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.50	-	
Weight			-	2.0	-	g
vveigni			-	0.07	-	OZ.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-247AC (JEDEC)	HFA32PA120C			



HEXFRED® V Ultrafast Soft Recovery Diode, 2 x 16 A

Vishay High Power Products



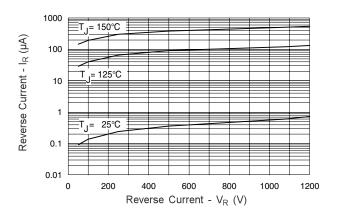


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

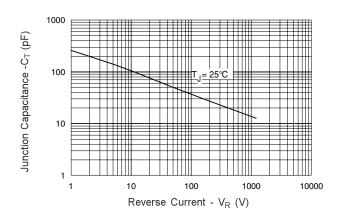


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

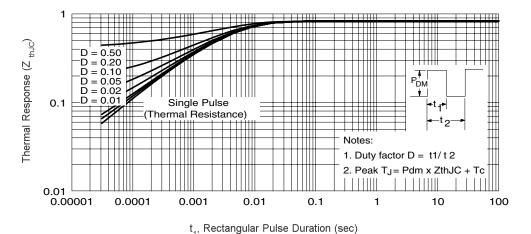


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

Vishay High Power Products

HEXFRED® Ultrafast Soft Recovery Diode, 2 x 16 A



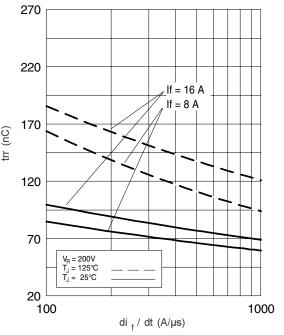


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

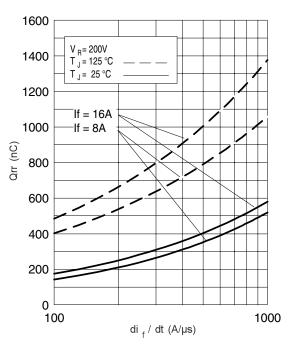


Fig. 7 - Typical Stored Charge vs. dI_F/dt (Per Leg)

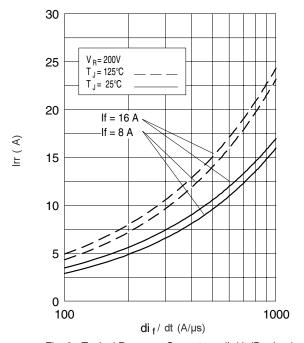


Fig. 6 - Typical Recovery Current vs. dI_F/dt (Per Leg)

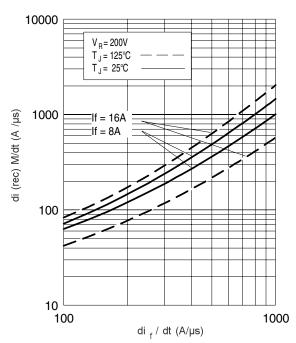


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt (Per Leg)



HEXFRED® Ultrafast Soft Recovery Diode, 2 x 16 A

Vishay High Power Products

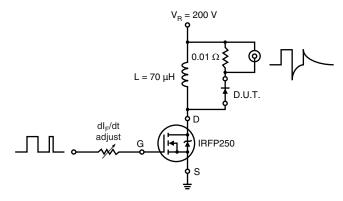
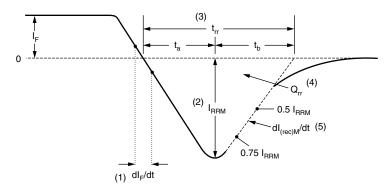


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- $\begin{array}{l} \text{(3) } \textbf{t}_{\text{rr}} \text{ reverse recovery time measured} \\ \text{from zero crossing point of negative} \\ \text{going I}_{\text{F}} \text{ to point where a line passing} \\ \text{through 0.75 I}_{\text{RRM}} \text{ and 0.50 I}_{\text{RRM}} \\ \text{extrapolated to zero current.} \end{array}$
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

HFA32PA120C

Vishay High Power Products

HEXFRED® Ultrafast Soft Recovery Diode, 2 x 16 A



ORDERING INFORMATION TABLE

Device code

HF	A	32	PA	120	С	-
1	2	3	4	5	6	7

- 1 HEXFRED® family
- Process designator: A = Subs. electron irradiated
 B = Subs. platinum
- 3 Current rating (32 = 32 A)
- 4 Package outline (PA = TO-247, 3 pins)
- 5 Voltage rating (120 = 1200 V)
- 6 Configuration (C = Center tap common cathode)
- 7 • None = Standard production
 - PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS				
Dimensions http://www.vishay.com/doc?95223				
Part marking information	http://www.vishay.com/doc?95226			

Document Number: 93095 Revision: 29-Jul-08

6



Vishay

Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.

Document Number: 91000 Revision: 18-Jul-08